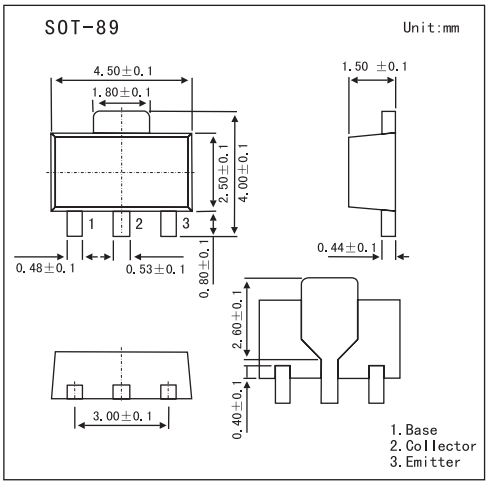
NPN Epitaxial Planar Silicon Transistor

2SC4984



■ Features

- Large current capacity.
- Low collector-to-emitter saturation voltage.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	15	V
Collector-emitter voltage	V_{CEO}	15	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	1.5	A
Collector current (pulse)	I_{CP}	3	A
Base current	I_B	300	mA
Collector dissipation,mounted on ceramic board($250mm^2$X0.8mm)	P_C	1.3	W
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

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■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	V_{CB} = 12 V, I_E=0			100	nA
Emitter cutoff current	I_{EBO}	V_{EB} = 4 V, I_C=0			100	nA
DC current gain	h_{FE}	V_{CE} = 2V , I_C = 50mA	140		560	
Gain bandwidth product	f_T	V_{CE} = 2V , I_C = 50mA		200		MHz
Output capacitance	C_{ob}	V_{CB} = 10V , f = 1.0MHz		10		pF
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = 5 mA , I_B = 0.5 mA		10	25	mV
		I_C = 500 mA , I_B = 25 mA		120	240	
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C = 500 mA , I_B = 25 mA		0.9	1.2	mV
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C = 10μA , I_E = 0	15			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C = 1mA , R_{BE} = ∞	15			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E = 10μA , I_C = 0	5			V

■ h_{FE} Classification

Marking	CT		
Rank	S	T	U
hFE	140～280	200～400	280～560